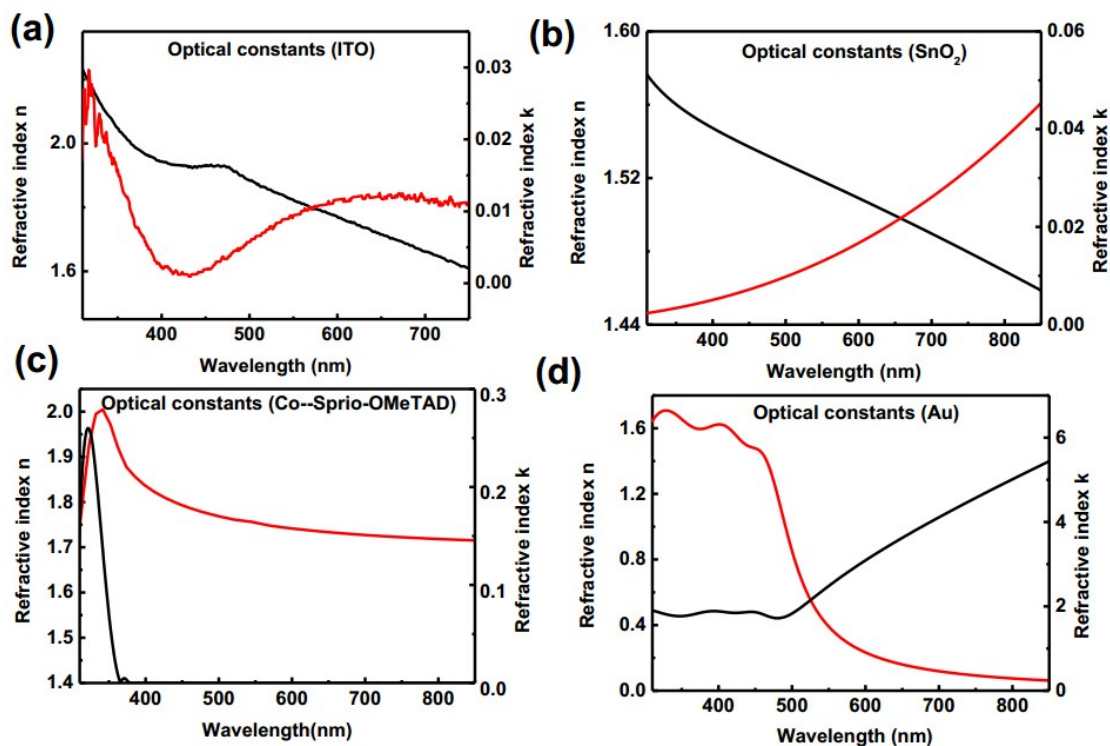


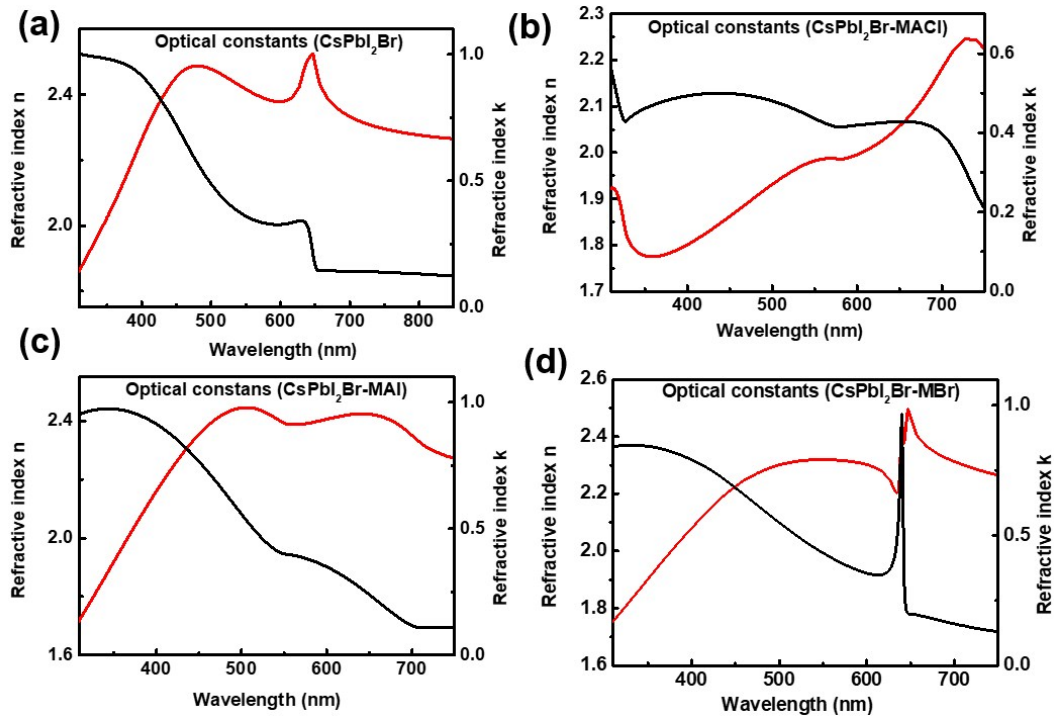
A Surface Modifier Enhances Performance in All-Inorganic CsPbI₂Br Perovskite Solar Cells with Efficiencies Approaching 15%

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Function layer	Material	Thickness d (nm)
Electrode	ITO	75nm
ELFs	SnO ₂	28 nm
Electrode	Au	60 nm
HLFs	Spiro-OMETAD	30 nm

Fig. S1. Optical constants used for the simulation of perovskite solar cells (PSC). (a) ITO, (b) SnO₂, and (c) Spiro-OMETAD (Co), and (d) Au used as input for the optical analysis. Also shown in the associated table are the thicknesses of different functional layers determined by profilometry.



	Material	Thickness d (nm)
	CsPbI ₂ Br	439 nm
CsPbI ₂ Br	CsPbI ₂ Br-MABr	441 nm
-MAX (Cl, I, Br)	CsPbI ₂ Br-MACl	449 nm
	CsPbI ₂ Br-MAI	441 nm

Fig. S2. Angle-varied spectroscopic ellipsometry measurements used for the simulation of perovskite solar cells. Optical constants of CsPbI₂Br PSCs with different passivation layers used as input parameters for the optical analysis and full simulation of solar cells. (a) CsPbI₂Br, (b) CsPbI₂Br-MABr, (c) CsPbI₂Br-MACl, and (d) CsPbI₂Br-MAI. In the associated table, thicknesses of active layer and MAX measured from a step profiler are summarized.

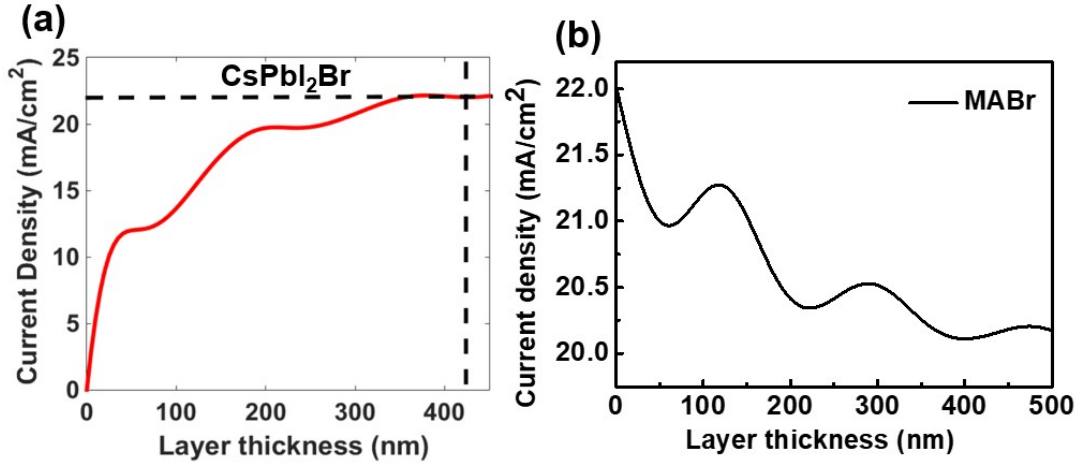


Fig. S3. Calculated photocurrent in different positions inside the CsPbI₂Br perovskite solar cells (a) without and (b) with MABr passivation layer (Current density obtained by from 100% IQE).

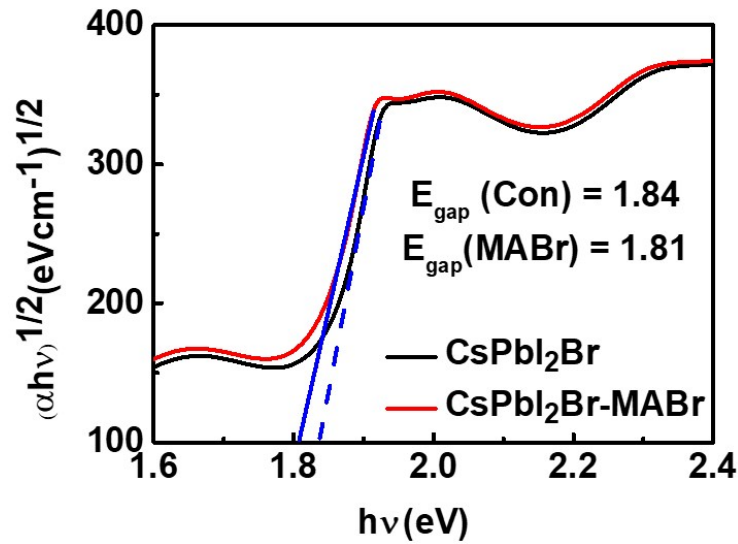


Fig. S4. UV-Vis absorption spectra of the CsPbI₂Br and CsPbI₂Br-MABr film (Tauc method). $h\nu = 1240/\lambda$

, absorption coefficient spectrum: $\alpha = \frac{1}{d} \times \ln(1/T)$, d is thickness of active layer. The picture of Tauc, $(\alpha h\nu)^{1/2} \sim h\nu$, the unit of α is cm^{-1} and the unit of $h\nu$ is eV.

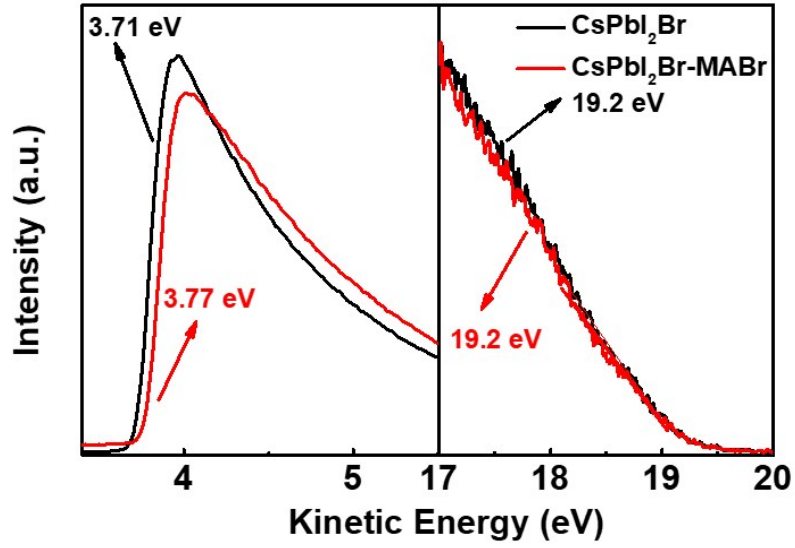


Fig. S5. UPS spectra measured on CsPbI₂Br and CsPbI₂Br-MABr films. Work function ϕ : $h\nu - \phi = E_{feimi} - E_{cutoff}$, $h\nu = 21.2\text{eV}$ and the value of E_{feimi} from the Au.

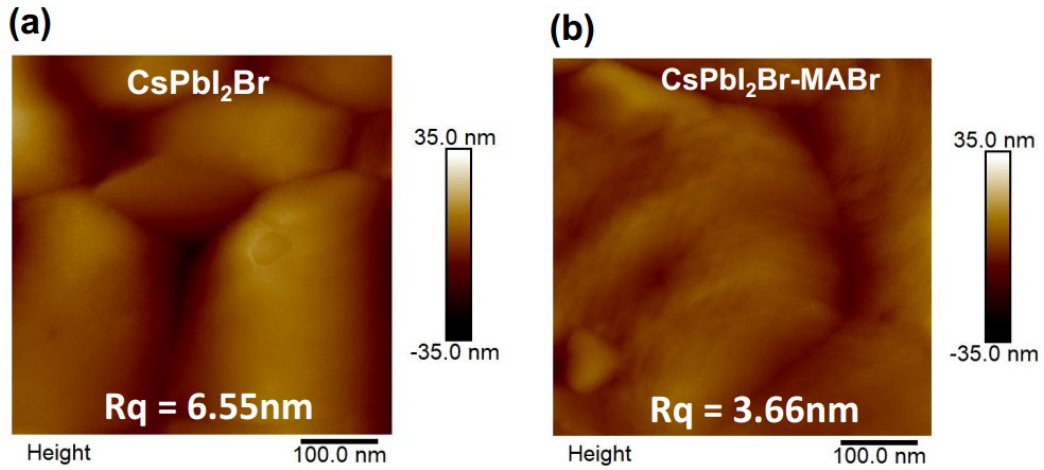


Fig. S6. Topographic images of (a) CsPbI₂Br and (b) CsPbI₂Br-MABr films measured at the grain boundaries with atomic force microscopy.

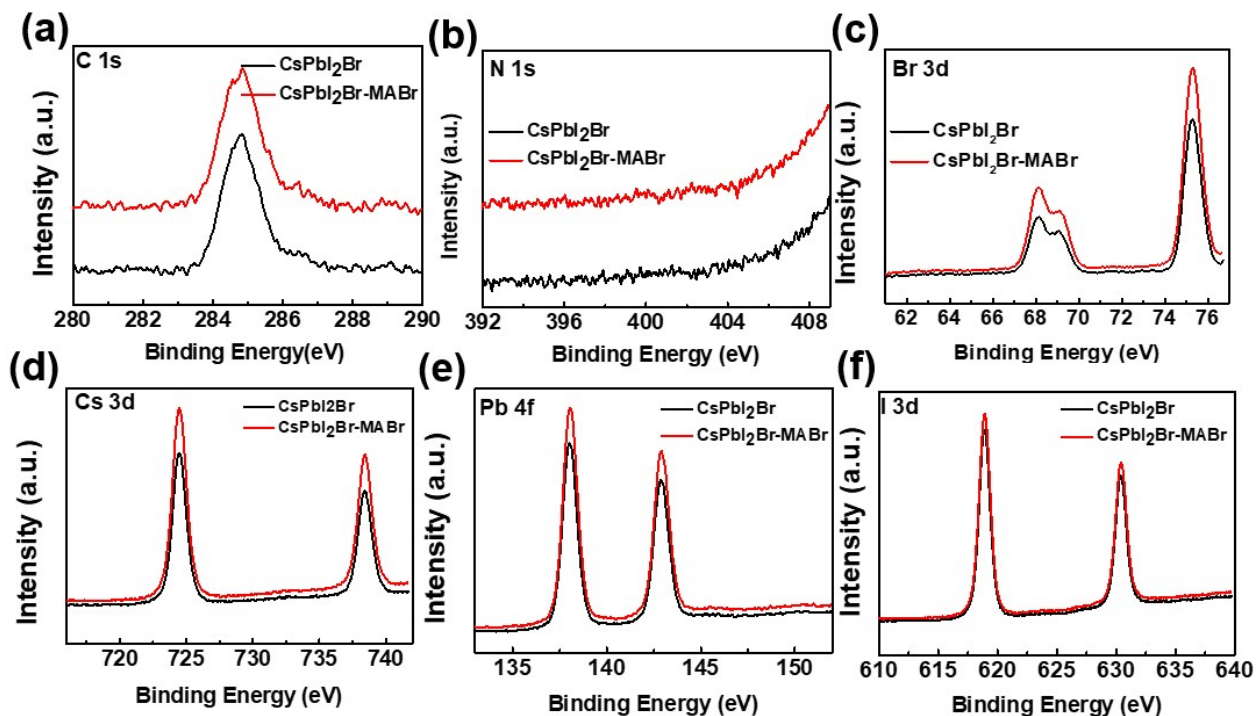


Figure. S7. High resolution XPS of CsPbI₂Br and CsPbI₂Br-MABr probed on core-level (a) C 1s, (b) N 1s, (c) Br 3d, (d) Cs 3d, (e) Pb 4f and (f) I 3d.

Table. S1. The statistical analysis of element contents on the surface of CsPbI₂Br-MABr thin films.

	Element	Br 3d	Pb 4f	C 1s	I 3d	Cs 3d
CsPbI ₂ Br	wt.%	13.6	13.3	22.2	29.5	17.6
CsPbI ₂ Br-MABr	wt.%	16.3	13.0	21.2	27.0	19.0

Table. S2. Device parameters along statistics of CsPbI₂Br solar cells prepared by passivation methods measured in the reverse scan directions under AM 1.5 G solar illumination.

Processing	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
CsPbI ₂ Br	1.20 (± 0.2)	14.1 (± 0.3)	68.4 (± 2)	12.8 (± 1)
CsPbI ₂ Br-MABr	1.23 (± 0.1)	14.9 (± 0.2)	79.2 (± 3)	14.0 (± 0.8)

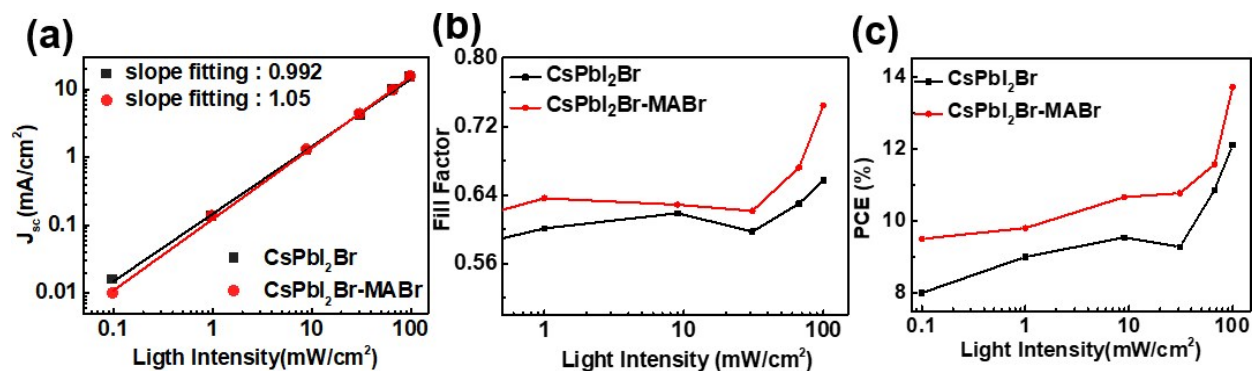


Fig. S8. Light intensity-dependent (a) Short-circuit current, (b) Fill factor, (c) Power conversion efficiency of CsPbI₂Br and CsPbI₂Br-MABr solar cells.

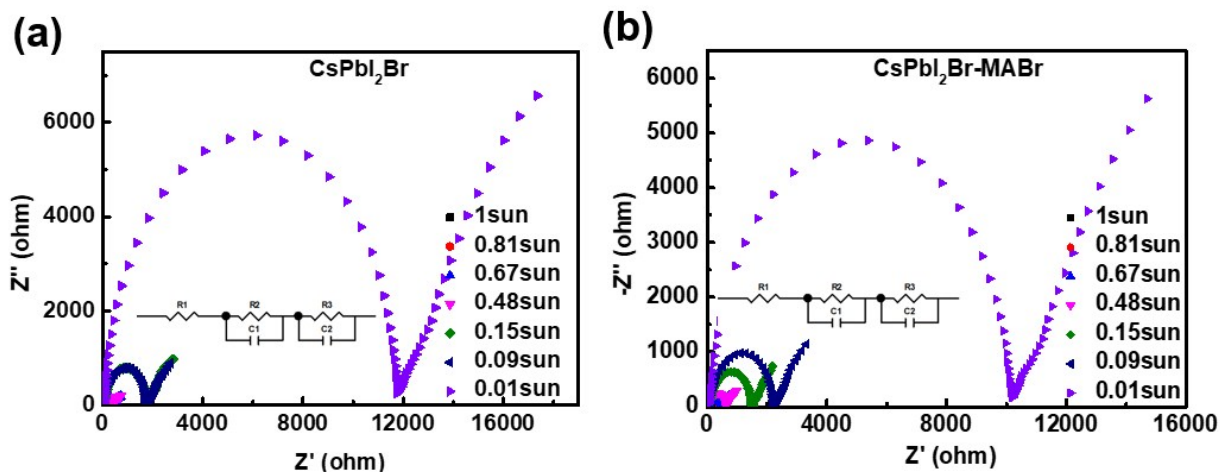


Fig. S9. Impedance spectra of CsPbI₂Br solar cells with and without MABr passivation layers measured at different light intensities (P_{light}).

Table. S3. Device parameters of impedance spectroscopy of CsPbI₂Br and CsPbI₂Br-MABr solar cells measured under 1 sun at V_{oc} together.

	R_1 (Ω)	R_2 (Ω)	R_3 (Ω)	C_1 (F)	C_2 (F)
CsPbI ₂ Br	48.6 (\pm 4)	207 (\pm 1)	19.3 (\pm 6)	7.63 (\pm 0.3) $\times 10^{-9}$	0.0023 (\pm 0.001)
CsPbI ₂ Br-MABr	64.9 (\pm 3)	194 (\pm 6)	251 (\pm 1)	5.16 (\pm 0.3) $\times 10^{-9}$	0.0030 (\pm 0.001)

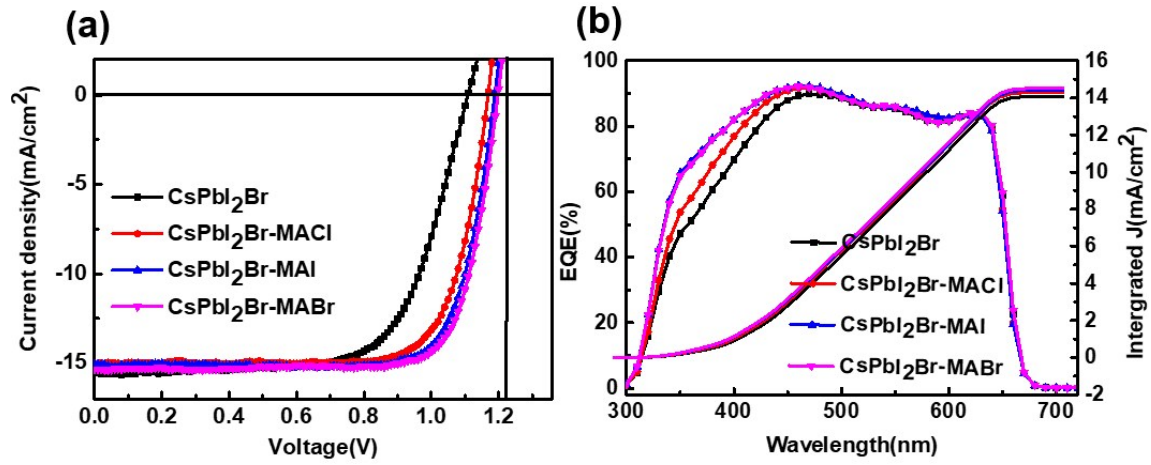


Fig. S10. (a) J-V characteristics of best CsPbI₂Br and CsPbI₂Br-MAX (X = Cl, Br, and I) solar under simulated AM 1.5G illumination (100 mW/cm²), (b) EQE spectra of according devices.

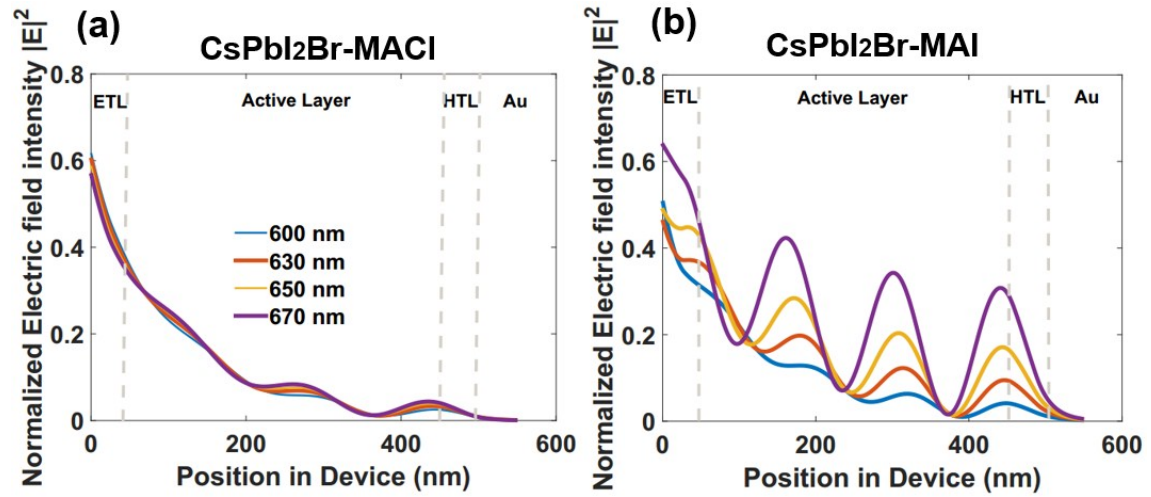


Fig. S11 (a-b) Simulated electric field intensities induced by propagation of various wavelengths of light through (a) CsPbI₂Br-MACl, (b) CsPbI₂Br-MAI.